

## EAST Search History

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	99	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface with germanium and bipolar and collector and emitter and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 21:58
L3	83	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 21:59
L4	83	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 21:59
L5	74	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/12/10 21:59
L6	64	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN."	US-PGPUB; USPAT	OR	ON	2009/12/10 21:59
L7	7	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN."	US-PGPUB; USPAT	OR	ON	2009/12/10 22:00
L8	18	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN."	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:00

L9	9	("20010003667"   "20020132438"   "20030189239"   "3725161"   "3725161"   "6437376"   "6586297"   "6437376"   "6686250").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2009/12/10 22:00
L10	236	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:05
L11	257144	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor and substrate and semiconductor and heterojunction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:06
L12	170	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor and substrate and semiconductor and heterojunction	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:06
L13	0	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor and substrate and semiconductor and heterojunction and ge- enriched	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:07
L14	0	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor and substrate and semiconductor and heterojunction and germanium-enriched	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:07

L15	1	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor and substrate and semiconductor and heterojunction and enriched	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:07
L16	52	(@ad<"20040310" @rlad<"20040310") and silicon near germanium near base and surface and germanium and bipolar and collector and emitter and transistor and substrate and semiconductor and heterojunction and 257/197,198,e29.033, e29.188.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 22:09
S1	5	("20030189239"   "3725161"   "6437376"   "6686250").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 16:52
S2	397	((ge germanium) near (rich enriched concentration) ge- enriched ) and bipolar near transistor and collector and emitter and base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 18:23
S3	221	((ge germanium) near (rich enriched concentration) ge- enriched ) and heterojunction near bipolar near transistor and collector and emitter and base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 18:24
S4	212	((ge germanium) near (rich enriched concentration) ge- enriched ) and heterojunction near bipolar near transistor and collector same emitter same base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 18:24
S5	19	((ge germanium) near (rich enriched high near concentration) ge-enriched ) and heterojunction near bipolar near transistor and collector same emitter same base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 18:24

S6	3	((ge germanium) near (rich enriched high near concentration) ge-enriched ) with base and heterojunction near bipolar near transistor and collector and emitter and base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 18:46
S7	19	((ge germanium) near (rich enriched high near concentration) ge-enriched ) with base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 18:56
S8	151	((ge germanium) near (rich enriched high near concentration) ge-enriched ) with sige and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 19:10
S9	30	((ge germanium) near (rich enriched high near concentration) ge-enriched ) with (silicon near germanium sige) and collector and emitter and base and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 19:10
S10	15	((ge germanium) near (rich enriched high near concentration) ge-enriched ) with (silicon near germanium sige) and collector and emitter and base and hbt and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 19:10
S11	2	"0490111"	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 19:16
S12	0	"ep0490111"	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 19:16
S13	16	pong-fei near lu	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 19:16
S14	21	"435135"	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 19:22

S15	2	"5089428".pn.	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 19:24
S16	22	"881669"	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 20:36
S17	2	"6624017".pn.	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 20:38
S18	4	"2005088721".pn.	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	ON	2008/10/31 20:43
S19	14	ge-enriched	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:03
S20	226	ge-rich	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:05
S21	92	ge-rich with sig	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:05
S22	80	ge-rich with sig and transistor	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:05
S23	1	ge-rich with sig with base with emitter and transistor	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:05
S24	0	ge-rich with sig with base with emitter and transistor and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:10
S25	0	ge-rich same sig same base same emitter and transistor and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:11
S26	2	ge near rich same sig same base same emitter and transistor and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:11
S27	9	ge near (rich concentration high) with surface same sig same base same emitter and transistor and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:15
S28	136	ge same sig same oxidized and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:20
S29	42	ge near (concentration rich enriched high) same sig same oxidized and (@ad<"20040310" @rlad<"20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:20

S30	7	ge near (concentration rich enriched high) same sige same oxidized and (@ad<"20040310"@rlad<"20040310") and hbt	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 21:21
S31	4	ge near (concentration rich enriched high) same sige same oxidized and (@ad<"20040310"@rlad<"20040310") and hbt and emitter and collector and base	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 22:00
S32	0	"6651697".pn. and S27	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 22:12
S33	1	"6651697".pn. and "13"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 22:12
S34	1	"6780725".pn. and "13"	US-PGPUB; USPAT; USOCR	OR	ON	2008/10/31 22:13
S35	0	h09288115	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2008/11/04 09:13
S36	2	"09288115"	US-PGPUB; USPAT; USOCR; JPO; DERWENT	OR	OFF	2008/11/04 09:13
S37	1	("6437376").PN. and "12"	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 11:36
S38	1	("6437376").PN. and (germanium ge)	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 13:07
S39	1	"3725161".pn. and (germanium ge)	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 13:13
S40	6	(US-20040031979-\$ or US-20040123882-\$ or US-20030189239-\$ or US-20020031893-\$).did. or (US-5106767-\$ or US-6780725-\$). did.	US-PGPUB; USPAT	OR	OFF	2008/11/07 14:38
S41	0	S40 and strain	USPAT	OR	OFF	2008/11/07 14:38
S42	0	S40 and strain\$4	USPAT	OR	OFF	2008/11/07 14:38
S43	0	"6437376".pn. and ev	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:16
S44	1	S40 and valence	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:16
S45	1	"6437376".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:18
S46	1	"6437376".pn. and emitter	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:19

S47	0	"6437376".pn. and emitter and band and gap and valence	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:22
S48	1	"6437376".pn. and emitter and band and gap	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:22
S49	20	valence near band with ev and hbt and sige	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:27
S50	17	valence near band with ev and hbt and sige and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:27
S51	41	band near gap with ev and hbt and sige and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:33
S52	1	"6437376".pn. and defect	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/07 15:37
S53	3	S40 and uniform	US-PGPUB; USPAT	OR	OFF	2008/11/07 15:58
S54	0	"3725161".pn. and surface	US-PGPUB; USPAT	OR	OFF	2008/11/07 16:14
S55	0	"3725161".pn. and (germanium ge)	US-PGPUB; USPAT	OR	OFF	2008/11/07 16:16
S56	0	"3725161".pn. and ge	US-PGPUB; USPAT	OR	OFF	2008/11/07 16:16
S57	1	"3725161".pn.	US-PGPUB; USPAT	OR	OFF	2008/11/07 16:17
S58	2	"3725161".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/11/07 16:17
S59	1	"3725161".pn. and (germanium ge)	US-PGPUB; USPAT; USOCR	OR	OFF	2008/11/07 16:17
S60	1	"6437376".pn. and substrate	US-PGPUB; USPAT; USOCR	OR	OFF	2008/11/07 16:35
S61	1	"20020132438".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/05/19 16:11
S62	1	"6617220".pn.	US-PGPUB; USPAT; USOCR	OR	ON	2009/05/19 16:12
S63	27	("4319932"   "4338138"   "4682409"   "4799099"   "4839305"   "4927774"   "4960726"   "5008207"   "5017990"   "5101256"   "5117271"   "5162245"   "5175607"   "5194926"   "5213989"   "5298786"   "5488002"   "5523245"   "5525818"   "5557131"   "5773350"   "5925923"   "6020246"   "6265276"   "6365451"   "6465317"   "6534372").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 17:31

S64	9	S63 and (germanium sig)	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 17:39
S65	1556	graded with (germanium sig)	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:05
S66	33	graded with (germanium sig) with base and (bjt bipolar near junction near transistor) and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:06
S67	5	("20030189239"   "3725161"   "3725161"   "6437376"   "6437376"   "6686250").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:15
S68	18	(rich enriched high near concentration) with (germanium sig) with base and (bjt bipolar near junction near transistor) and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:43
S69	5030831	(rich enriched high near concentration) with (germanium sig) (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:54
S70	928	(rich enriched high near concentration) with (germanium sig) and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:54
S71	508	(rich enriched) with (germanium sig) and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:55
S72	0	(rich enriched) with (germanium sig) with base with emitter and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:55
S73	21	concentration with profile with (germanium sig) with base with emitter and (@ad< "20040310" @rlad< "20040310")	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 19:55
S74	1	"6362065".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 21:40
S75	1	"5962880".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 21:41
S76	0	"5962880".pn. and ev	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 21:41
S77	1	"5962880".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 21:54



S78	1	"20020132438".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 21:57
S79	1	"6781214".pn. and "120"	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 22:04
S80	1	"20010003667".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 22:08
S81	1	"20020132438".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 22:18
S82	1	"6781214".pn. and "107"	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 22:24
S83	5	germanium same injection near2 interstitials	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 22:44
S84	0	germanium same injection near2 interstitials same (oxide oxidation)	US-PGPUB; USPAT; USOCR	OR	OFF	2009/05/19 22:46
S85	5	("20030189239"   "3725161"   "6437376"   "6686250").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/12/10 19:00
S86	63	(@ad<"20040310" @rlad<"20040310") and emitter near contact with germanium	US-PGPUB; USPAT; USOCR	OR	ON	2009/12/10 19:11
S87	4919	(@ad<"20040310" @rlad<"20040310") and emitter near contact enriched near germanium	US-PGPUB; USPAT; USOCR	OR	ON	2009/12/10 19:21
S88	1	(@ad<"20040310" @rlad<"20040310") and emitter near contact and enriched near germanium	US-PGPUB; USPAT; USOCR	OR	ON	2009/12/10 19:21
S89	2	(@ad<"20040310" @rlad<"20040310") and emitter and contact and enriched near germanium and silicon near germanium and collector and bipolar and transistor	US-PGPUB; USPAT; USOCR	OR	ON	2009/12/10 19:28
S90	2	(@ad<"20040310" @rlad<"20040310") and emitter and contact and enriched near germanium and silicon near germanium and collector and bipolar and transistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 19:28
S91	4	(@ad<"20040310" @rlad<"20040310") and "3725161".pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/12/10 19:31

12/ 10/ 2009 10:53:09 PM

C:\ Documents and Settings\ bliu2\ My Documents\ EAST\ Workspaces\ 10598213.wsp